

AMENDMENT TO THE SPECIFICATION

*Please replace paragraph [0022] of the specification with the following amended paragraph [0022]:*

[0022] Referring to Figure 7, the first oxide layer 26 underlying the ~~first~~ second nitride spacer 28 is etched using any well known etching process forming an undercut 30. Isotropic etching methods which may be used to form the undercut 30 include a hydrofluoric (HF) etch, for example. The etching process leaves the side edge of the first nitride spacer 24 exposed within the undercut 30. The etching process leaves the undercut 30 with a bottom surface of the second nitride spacer 28 and a bottom surface of the first oxide layer 26 bounding the top of the undercut 30.

*Please replace paragraph [0024] of the specification with the following amended paragraph [0024]:*

[0024] Accordingly, the first step 34 of the raised source/drain 32 is bounded on top by a lower surface of the second nitride spacer 28 and the first oxide layer 26. The side of the first step 34 closest to polysilicon gate 16 is bounded by ~~an~~ a side edge of the first nitride spacer 24. A lower surface of the first step 34 is bounded by the substrate 12. The upper surface of the second step 36 extends above the upper surface of the first step 34. The raised source/drain 32 may be formed using a selective epi growth process using any semiconductor material such as, for example, silicon, silicon germanium (SiGe) and silicon carbon (SiC).